1. General description

NPN/NPN matched double transistor in a very small Surface-Mounted Device (SMD) SOT363 (SC-88) plastic package. The transistors in the SOT363 package are fully isolated internally.

NPN/NPN hFE1/hFE2 0.98 complement: PMP4201Y

PNP/PNP complement: PMP5501Y

2. Features and benefits

- Current gain matching
- Base-emitter voltage matching
- Application-optimized pinout
- AEC-Q101 qualified

3. Applications

- Current mirror
- · Differential amplifier

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	45	V
I _C	collector current			-	-	100	mA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C		200	290	450	
Per device							
h _{FE1} /h _{FE2}	DC current gain matching	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	0.95	1	-	
V _{BE1} -V _{BE2}	base-emitter voltage matching		[2]	-	-	2	mV

- [1] The smaller of the two values is taken as the numerator.
- [2] The smaller of the two values is subtracted from the larger value.



45 V, 100 mA NPN/NPN matched double transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B1	base TR1		04 54 50
2	B2	base TR2	6 5 4	C1 E1 E2
3	C2	collector TR2		TR2
4	E2	emitter TR2		
5	E1	emitter TR1		B1 B2 C2 006aaa548
6	C1	collector TR1	TSSOP6 (SOT363)	3333437.0

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PMP4501Y		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMP4501Y	S8%

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	45	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	100	mA
I _{CM}	peak collector current	t _p ≤ 1 ms		-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device	·					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

10. Characteristics

Table 7. Characteristics

Parameter	Conditions		Min	Тур	Max	Unit
,				'		'
collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C		-	-	15	nA
current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C		-	-	5	μA
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
DC current gain	V _{CE} = 5 V; I _C = 10 μA; T _{amb} = 25 °C		-	250	-	
	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C		200	290	450	
collector-emitter	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C		-	50	200	mV
saturation voltage	I _C = 100 mA; I _B = 5 mA; T _{amb} = 25 °C		-	200	400	mV
base-emitter saturation	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C	[1]	-	760	-	mV
voltage	I _C = 100 mA; I _B = 5 mA; T _{amb} = 25 °C	[1]	-	910	-	mV
base-emitter voltage	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C	[2]	610	660	710	mV
	V _{CE} = 5 V; I _C = 10 mA; T _{amb} = 25 °C	[2]	-	-	770	mV
collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	1.5	pF
emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	11	-	pF
transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C		100	250	-	MHz
noise figure	V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 10 Hz to 15.7 kHz; T_{amb} = 25 °C		-	2.8	-	dB
	V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; B = 200 Hz; f = 1 kHz; T_{amb} = 25 °C		-	3.3	-	dB
				'		1
DC current gain matching	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$	[3]	0.95	1	-	
base-emitter voltage matching		[4]	-	-	2	mV
	collector-base cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage base-emitter voltage base-emitter voltage collector capacitance emitter capacitance transition frequency noise figure DC current gain matching base-emitter voltage	collector-base cut-off current $V_{CB} = 30 \text{ V; } I_E = 0 \text{ A; } T_{amb} = 25 \text{ °C}$ $V_{CB} = 30 \text{ V; } I_E = 0 \text{ A; } T_{j} = 150 \text{ °C}$ emitter-base cut-off current $V_{CB} = 5 \text{ V; } I_{C} = 0 \text{ A; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ µA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 100 \text{ mA; } I_{B} = 0.5 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 100 \text{ mA; } I_{B} = 0.5 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 0 \text{ A; } I_{e} = 0 \text{ A; } I_{e} = 10 \text{ MHz; } I_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } I_{E} = 10 \text{ mA; }$		$ \begin{array}{ c c c c c } \hline \text{current} & V_{CB} = 30 \text{ V; } I_E = 0 \text{ A; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CB} = 30 \text{ V; } I_E = 0 \text{ A; } T_j = 150 \text{ °C} \\ \hline \text{v}_{CB} = 30 \text{ V; } I_E = 0 \text{ A; } T_{j} = 150 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 0 \text{ A; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 10 \text{ µA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 100 \text{ mA; } I_{B} = 0.5 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 100 \text{ mA; } I_{B} = 0.5 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 2 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } T_{amb} = 25 \text{ °C} \\ \hline \text{v}_{CE} = 5 \text{ V; } I_{C} = 0 \text{ A; } I_{E} = 0$	$ \begin{array}{ c c c c c } \hline \text{collector-base cut-off} & V_{CB} = 30 \text{ V}; \ I_{E} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} & - & - & - & - & - & - & - & - & - & $	$ \begin{array}{ c c c c c } \hline \text{collector-base cut-off} \\ \text{current} \\ \hline \\ $

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

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^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] The smaller of the two values is taken as the numerator.

^[4] The smaller of the two values is subtracted from the larger value.

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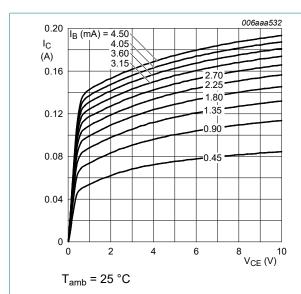
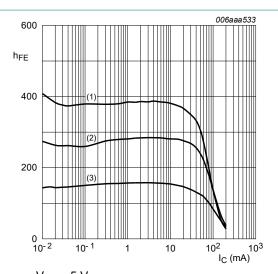


Fig. 1. Collector current as a function of collectoremitter voltage; typical values



V_{CE} = 5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

Fig. 2. DC current gain as a function of collector current; typical values

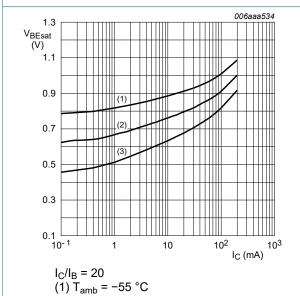
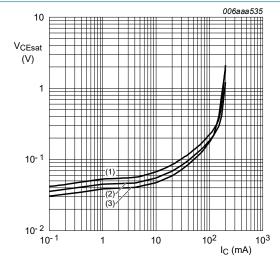


Fig. 3. Base-emitter saturation voltage as a function of collector current; typical values

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) T_{amb} = 100 °C



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = 100 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -55 \,^{\circ}C$

Fig. 4. Collector-emitter saturation voltage as a function of collector current; typical values

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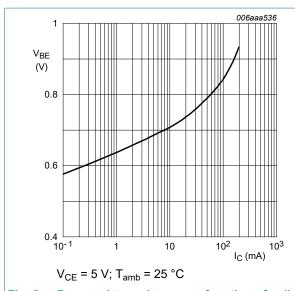


Fig. 5. Base-emitter voltage as a function of collector current; typical values

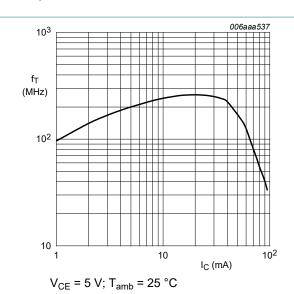


Fig. 6. Transition frequency as a function of collector current; typical values

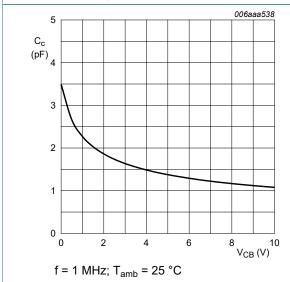
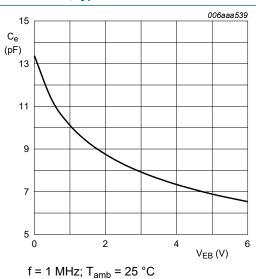
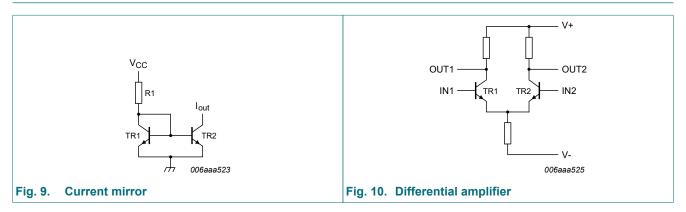


Fig. 7. Collector capacitance as a function of collectorbase voltage; typical values



8. Emitter capacitance as a function of emitterbase voltage; typical values

11. Application information



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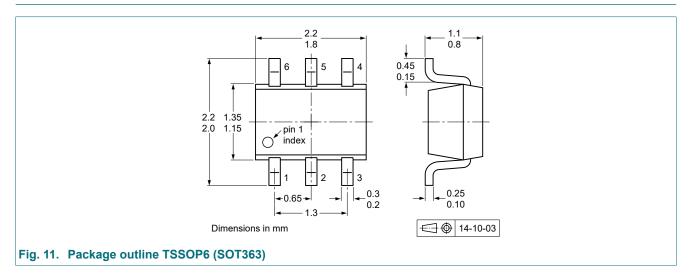
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12. Test information

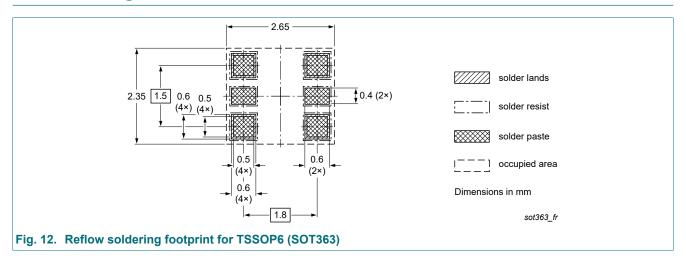
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

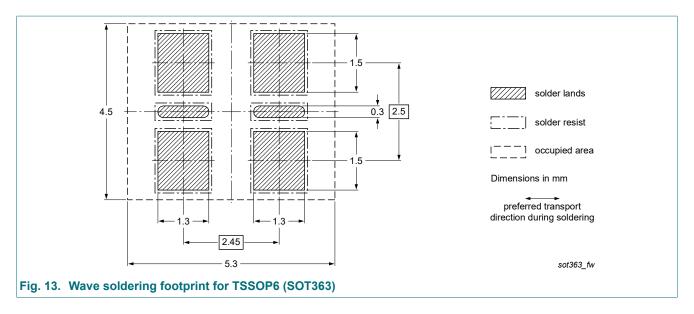
13. Package outline



14. Soldering



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15. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMP4501Y v.5	20221228	Product data sheet	-	PMP4501V_G_Y_4
Modifications:	Nexperia. • Legal texts ha	this data sheet has been redoved to the new on the new of the new		, ,
PMP4501V_G_Y_4	20090828	Product data sheet	-	PMP4501V_G_Y_3
PMP4501V_G_Y_3	20060919	Product data sheet	-	PMP4501G_Y_2
PMP4501G_Y_2	20060214	Product data sheet	-	PMP4501G_Y_1
PMP4501G_Y_1	20060202	Product data sheet	-	-

16. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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